

isc Silicon PNP Power Transistor
2SB568
DESCRIPTION

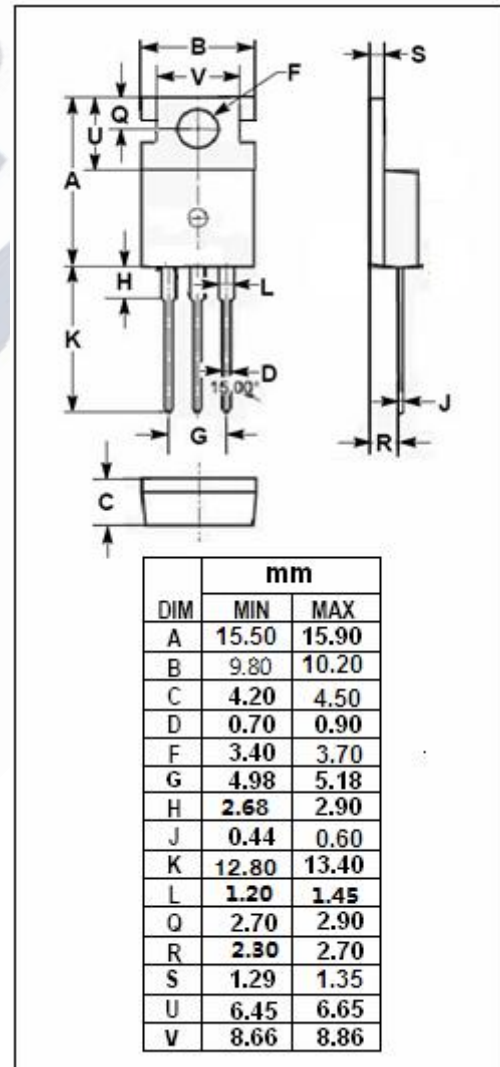
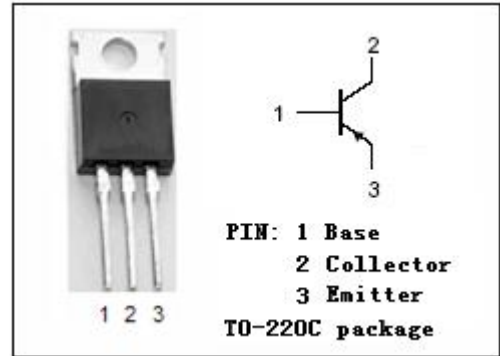
- Collector-Emitter Breakdown Voltage-
: $V_{(BR)CEO} = -150V(\text{Min.})$
- Low Collector Saturation Voltage-
: $V_{CE(sat)} = -2.0(\text{Max.}) @ I_C = -0.5A$
- Complement to Type 2SD478
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

APPLICATIONS

- Designed for TV vertical deflection output applications.

ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)

SYMBOL	PARAMETER	VALUE	UNIT
V_{CBO}	Collector-Base Voltage	-200	V
V_{CEO}	Collector-Emitter Voltage	-150	V
V_{EBO}	Emitter-Base Voltage	-6	V
I_C	Collector Current-Continuous	-2	A
I_{CM}	Collector Current-Peak	-5	A
P_C	Collector Power Dissipation@ $T_c=25^\circ\text{C}$	30	W
	Collector Power Dissipation@ $T_a=25^\circ\text{C}$	1.8	
T_J	Junction Temperature	150	$^\circ\text{C}$
T_{stg}	Storage Temperature	-45~150	$^\circ\text{C}$



isc Silicon PNP Power Transistor**2SB568****ELECTRICAL CHARACTERISTICS****T_j=25°C unless otherwise specified**

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	I _C = -50mA; R _{BE} = ∞	-150			V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	I _E = -5mA; I _C = 0	-6			V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	I _C = -0.5A; I _B = -50mA			-2.0	V
V _{BE(on)}	Base-Emitter On Voltage	I _C = -50mA; V _{CE} = -4V			-1.0	V
I _{CBO}	Collector Cutoff Current	V _{CB} = -120V; I _E = 0			-1.0	μ A
h _{FE-1}	DC Current Gain	I _C = -50mA; V _{CE} = -4V	60		320	
h _{FE-2}	DC Current Gain	I _C = -0.5A; V _{CE} = -4V	60			
C _{OB}	Output Capacitance	I _E = 0; V _{CB} = -10V; f= 1MHz		22		pF

◆ h_{FE-1} Classifications

B	C	D
60-120	100-200	160-320